



Future Normal in Semiconductor

2025-02-13(목), 15:50-17:20

좌장: 추후업데이트 예정

E. Compound Semiconductors 분과

[TN3-E] WBG Semiconductor-III

<p>TN3-E-1 15:50-16:05</p>	<p>Vertically Integrated Active Power Delivery Network (PDN) with Direct Heat Spreading Layer Bonding Chan Jik Lee¹, Jaeyong Jeong¹, Sung Joon Choi¹, Nahyun Rheem¹, Minseo Song¹, Yoon-Je Suh¹, Bong Ho Kim¹, Joon Pyo Kim¹, Joonsup Shim¹, Sanghyeon Kim¹, Jiseon Lee², Myungsoo Park², Yumin Koh², and Donghyun Kim² ¹KAIST, ²Korea Advanced Nano Fab Center</p>
<p>TN3-E-2 16:05-16:20</p>	<p>Physically Unclonable Function Using Bismuth Sulfide and Doping of Self-Assembled Monolayer Heebeen Shin, Hocheon Yoo, and Dong Hyun Lee Gachon University</p>
<p>TN3-E-3 16:20-16:35</p>	<p>6/8inch-SiC Single Crystals Obtained with Modification of Crucible Structure and Process Condition in PVT Growth Jung Gyu Kim¹, Kap Ryeol Ku¹, and Won Jae Lee² ¹ Senic Co. Ltd., ²Department of Advanced Materials Engineering, Dong-Eui University</p>
<p>TN3-E-4 16:35-16:50</p>	<p>Sn-doped α-Ga₂O₃ Quasi-vertical Schottky Barrier Diode Fabrication by Mist-CVD Jang Hyeok Park¹, Ho Jung Jeon¹, You Seung Rim^{1,2}, Jung Yeop Hong³, Jung Hee Park³, and Young Kyun Jung³ ¹Department of Semiconductor System Engineering and Intelligent Convergence Drone, ²Institute of Semiconductor and System IC, Sejong University, ³Energy Devices Research Team, Research and Development Division, Hyundai Motor Group</p>
<p>TN3-E-5 16:50-17:05</p>	<p>고속 스위칭 환경에서 1.2 kV SiC MOSFET의 전기적 특성 변화 분석 윤효원¹, 김상엽², 백두산¹, 강규혁², 박수민¹, 박가영¹, 석오균¹ ¹부산대학교, ²국립금오공과대학교</p>
<p>TN3-E-6 17:05-17:20</p>	<p>Physically Driven Curve Modulation of Gaussian Transistor based on DNTT/IGZO Heterostructure Anti-ambipolar Operation Jisoo Park¹ and Hocheon Yoo^{1,2} ¹Department of Semiconductor Engineering, Gachon University, ²Department of</p>



제 32회 한국반도체학술대회

The 32nd Korean Conference on Semiconductors

2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

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Electronic Engineering, Gachon University
